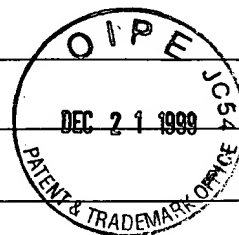


FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.061DV1	APPLICATION NO. 09/397,952
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT AHMAD	
		FILING DATE September 17, 1999	GROUP 2814



U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
SR	4,839,301	06/13/89	Lee			
	4,996,081	2/26/91	Ellul, et al.			
	5,057,499	10/15/91	Lowrey et al.			
	5,073,509	12/17/91	Lee			
	5,177,027	1/5/93	Lowrey et al.			
	5,240,874	8/31/93	Roberts			
	5,264,724	11/23/93	Brown et al.			
	5,266,510	11/30/93	Lee			
	5,272,367	12/21/93	Dennison et al.			
	5,341,016	08/23/94	Prall et al.			
	5,345,104	09/06/94	Prall et al.			
	5,349,494	9/20/94	Ando			
	5,360,769	11/01/94	Thakur et al.			
	5,376,593	12/27/94	Sandhu et al.			
	5,378,641	1/3/95	Cheffings			
	5,393,683	2/28/95	Mathews, et al.			
	5,405,791	4/11/95	Ahmad et al.			
	5,407,870	4/18/95	Okada et al.			
	5,429,972	7/4/95	Anjum et al.			
	5,463,234	10/95	Toriumi et al.	257	410	
	5,472,896	12/05/95	Chen et al.			
	5,811,865	9/98	Hodges et al.	257	411	5/94

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
SR	Shimizu, et al. "Impact of Surface Proximity Gettering and Nitrided Oxide Side-Wall Spacer by Nitrogen Implantation on Sub-Quarter Micron CMOS LDD FETs", IEDM 95, pp. 859-62 (1995).

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EXAMINER	DATE CONSIDERED
	July 18/2002

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.